



Docket: T00-338
S/N 09/785,114

Amendment

In response to the above mentioned Office action please amend the spec and claims as follows:

CLEAN VERSION

In the Specification

In the specification

Please replace the 1st full Paragraph on spec p. 10 with the following rewritten paragraph:

a¹
In a critical step in the invention, as shown in FIG 3, we form a mask (e.g., resist) pattern 56 over the cell node 40. Any implant blocking mask can be used. This resist pattern serves to block a subsequent high concentration (e.g., P+) implant into the node cell region.

Please replace the 2nd full Paragraph on spec p. 12 with the following rewritten paragraph:

a²
The bit line region 34 60 consists of a first bit line region 34 and a second bit line region 60. The first bit line region 34 has about the same impurity concentration as the cell node 40.

In the Claims

Please amend the claims as follows:

1.(AMENDED) A method of fabrication of a 1T Static Random Access Memory (SRAM), comprising the steps of:

- a³
Puh
B1
- a) forming a word line structure and a capacitor plate structure on a substrate;
 - (1) said capacitor plate structure comprised of a capacitor dielectric on said substrate and a conductive plate layer on said capacitor dielectric; said

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